

Thyristor \ Diode Module

$V_{RRM} = 2 \times 1600 \text{ V}$

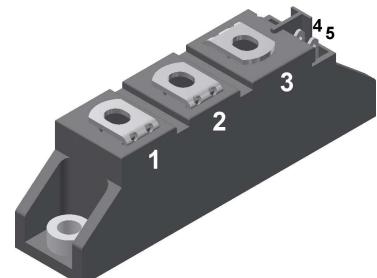
$I_{TAV} = 27 \text{ A}$

$V_T = 1.27 \text{ V}$

Phase leg

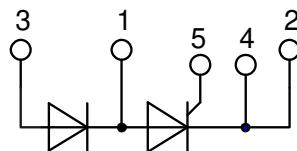
Part number

MCD26-16io1B



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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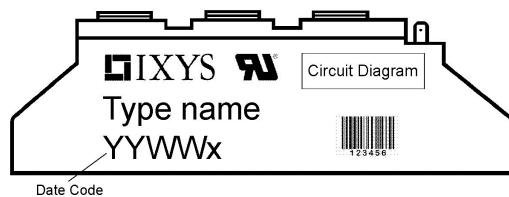
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Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1600 V$ $V_{R/D} = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		100 3	μA mA
V_T	forward voltage drop	$I_T = 40 A$	$T_{VJ} = 25^\circ C$		1.27	V
		$I_T = 80 A$			1.64	V
		$I_T = 40 A$	$T_{VJ} = 125^\circ C$		1.27	V
		$I_T = 80 A$			1.65	V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 125^\circ C$		27	A
$I_{T(RMS)}$	RMS forward current	180° sine			42	A
V_{T0}	threshold voltage	r_T slope resistance } for power loss calculation only	$T_{VJ} = 125^\circ C$		0.85	V
	slope resistance				11	$m\Omega$
R_{thJC}	thermal resistance junction to case				0.88	K/W
R_{thCH}	thermal resistance case to heatsink			0.2		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		115	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		520	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		560	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 125^\circ C$		440	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		475	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		1.35	kA^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		1.31	kA^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 125^\circ C$		970	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		940	A^2s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	22		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^\circ C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ C; f = 50 \text{ Hz}$	repetitive, $I_T = 45 A$		150	$A/\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$				
		$I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 27 A$		500	$A/\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		1000	$V/\mu s$
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		1.5	V
			$T_{VJ} = -40^\circ C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		100	mA
			$T_{VJ} = -40^\circ C$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10 \mu s$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		450	mA
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ C$		2	μs
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 20 A; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 100^\circ C$ $di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$		150		μs

Package TO-240AA
Ratings

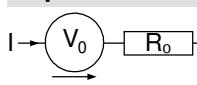
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	<i>RMS current</i>	per terminal			200	A
T_{VJ}	<i>virtual junction temperature</i>		-40		125	°C
T_{op}	<i>operation temperature</i>		-40		100	°C
T_{stg}	<i>storage temperature</i>		-40		125	°C
Weight				81		g
M_D	<i>mounting torque</i>		2.5		4	Nm
M_T	<i>terminal torque</i>		2.5		4	Nm
$d_{Spp/App}$	<i>creepage distance on surface / striking distance through air</i>		<i>terminal to terminal</i>	13.0	9.7	mm
$d_{Spb/Apb}$			<i>terminal to backside</i>	16.0	16.0	mm
V_{ISOL}	<i>isolation voltage</i>	$t = 1 \text{ second}$ $t = 1 \text{ minute}$ 50/60 Hz, RMS; $I_{ISOL} \leq 1 \text{ mA}$		4800		V
				4000		V

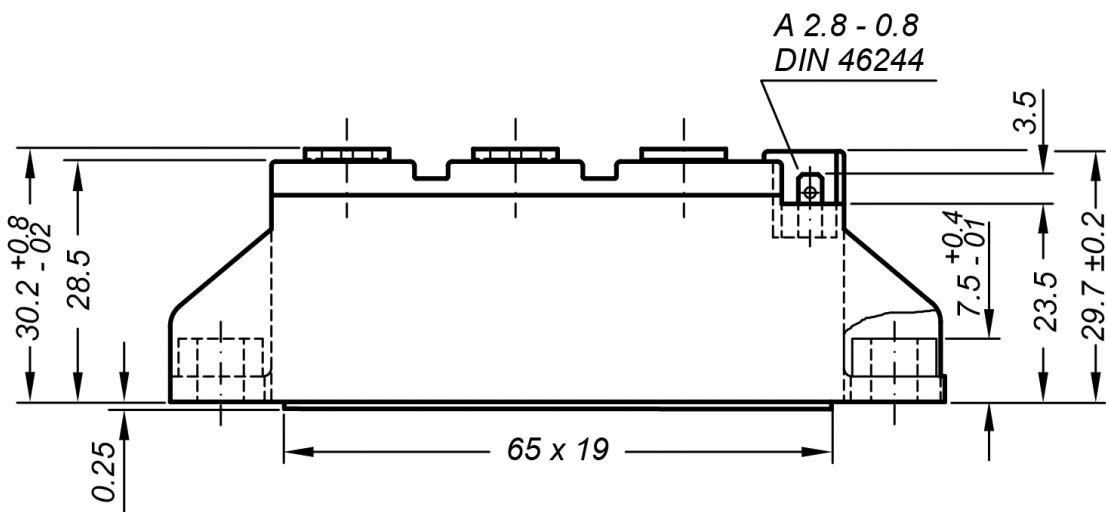
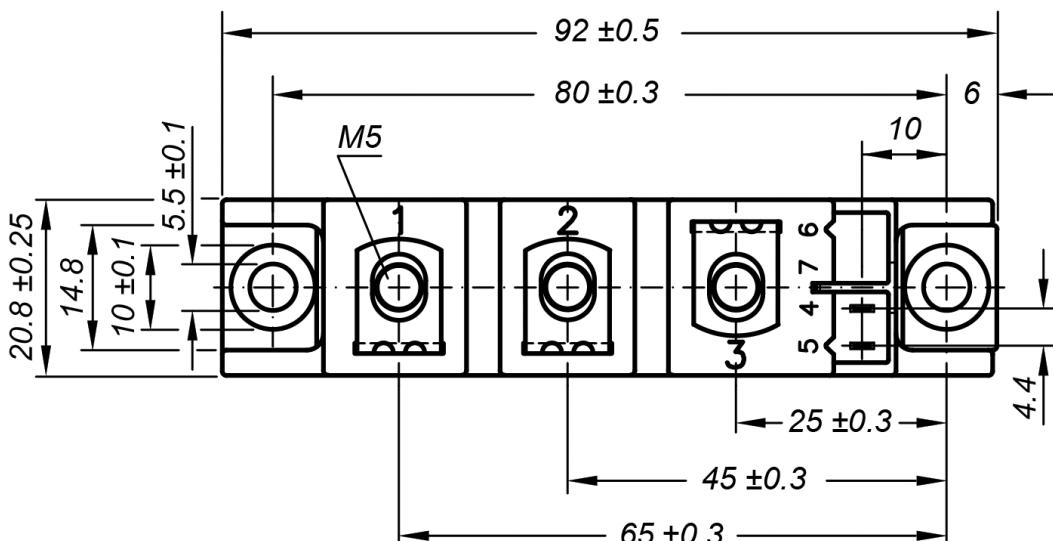


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD26-16io1B	MCD26-16io1B	Box	36	500955

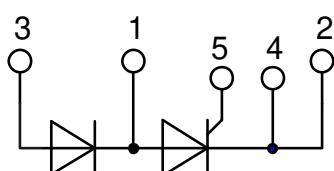
Similar Part	Package	Voltage class
MCMA35PD1600TB	TO-240AA-1B	1600
MCMA50PD1600TB	TO-240AA-1B	1600

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 125^\circ\text{C}$

	Thyristor	
V_0		
$V_{0\max}$	<i>threshold voltage</i>	0.85 V
$R_{0\max}$	<i>slope resistance *</i>	9.8 mΩ

Outlines TO-240AA

General tolerance: DIN ISO 2768 class „c“

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor

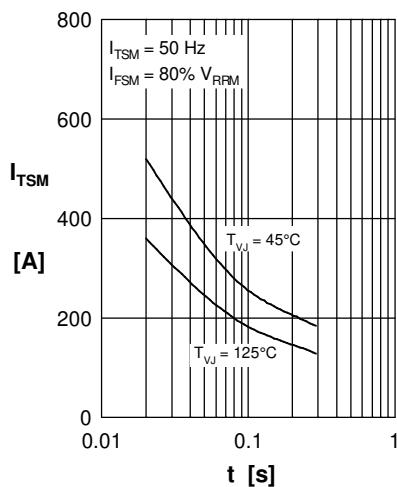


Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t: duration

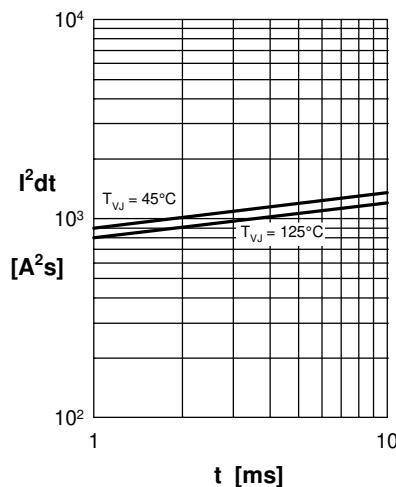


Fig. 2 I^2t versus time (1-10 ms)

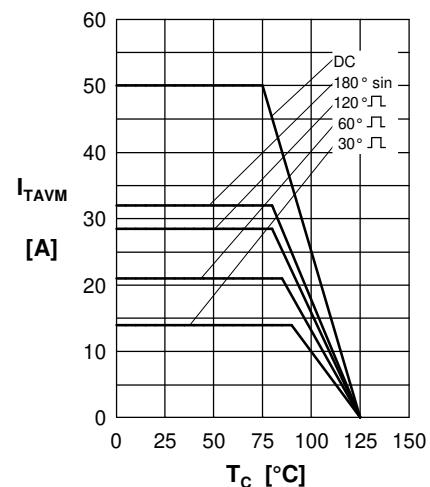


Fig. 3 Max. forward current
at case temperature

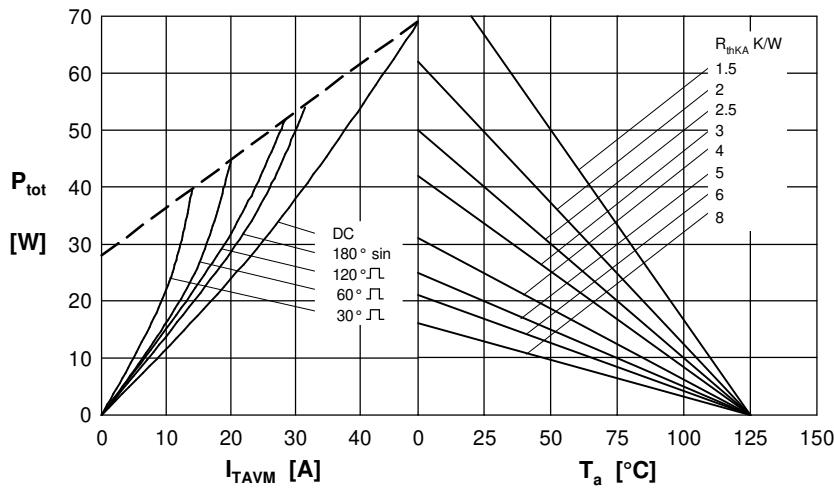


Fig. 4 Power dissipation vs. on-state current & ambient temperature
(per thyristor or diode)

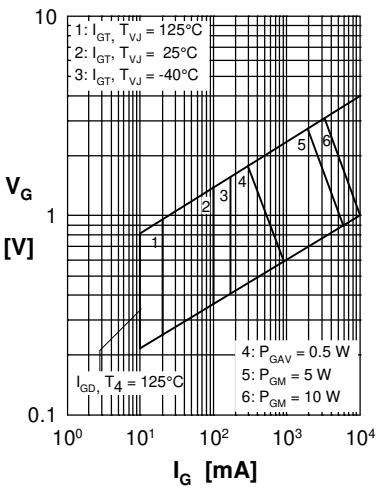


Fig. 5 Gate trigger characteristics

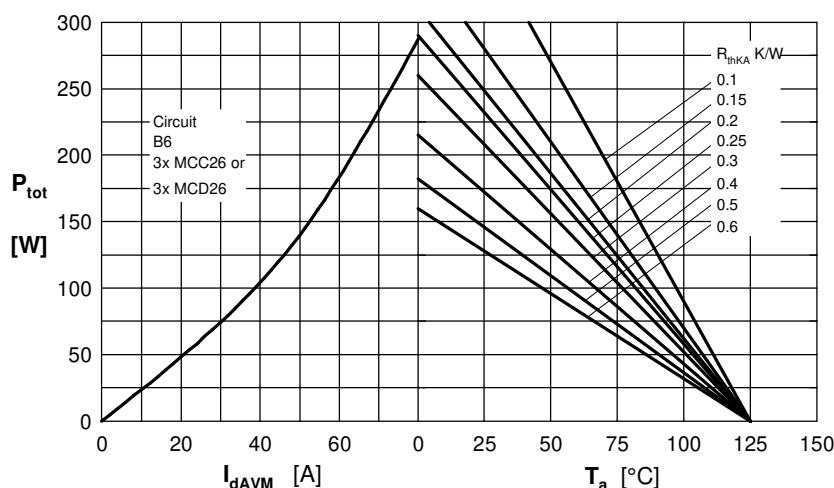


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct
output current and ambient temperature

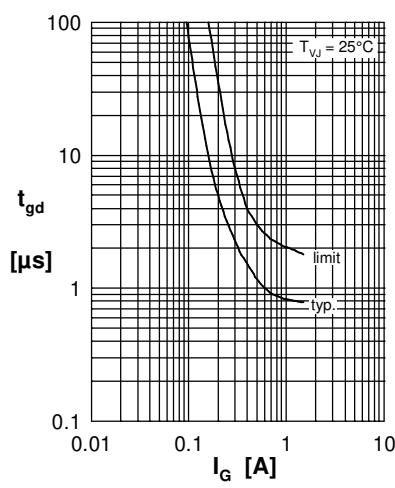


Fig. 7 Gate trigger delay time

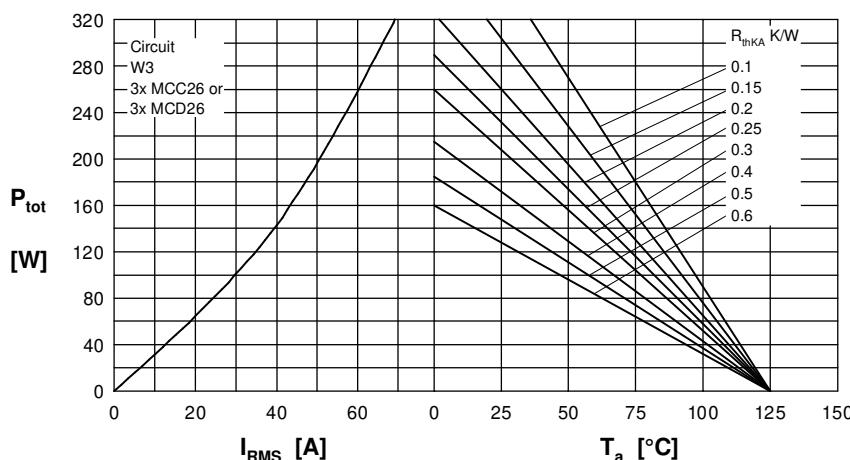
Rectifier


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

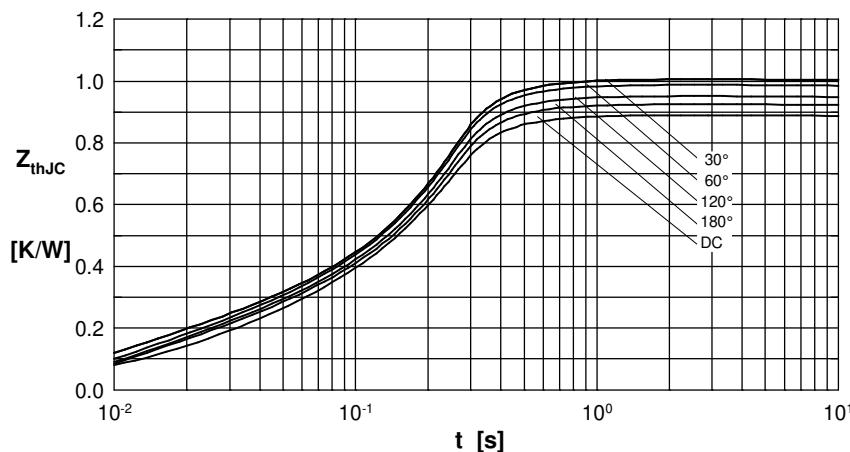


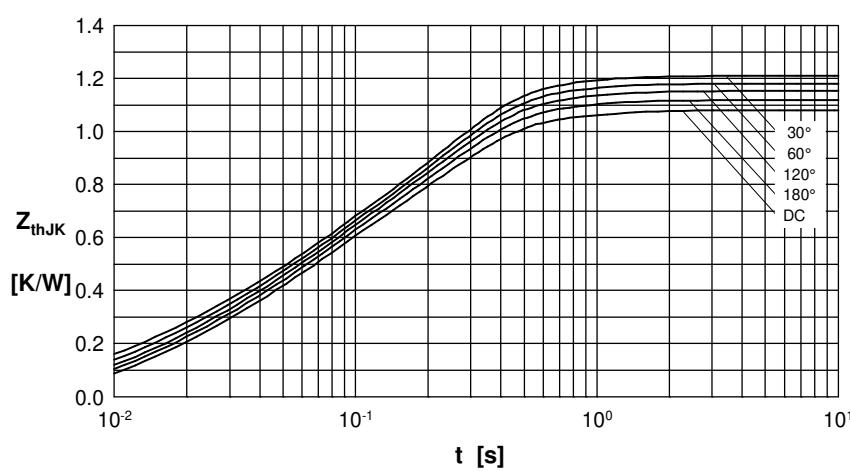
Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduction angles d:

d	R _{thJC} [K/W]
DC	0.88
180°	0.92
120°	0.95
60°	0.98
30°	1.01

Constants for Z_{thJC} calculation:

i	R _{thi} [K/W]	t _i [s]
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.1910



R_{thJK} for various conduction angles d:

d	R _{thJK} [K/W]
DC	1.08
180°	1.12
120°	1.15
60°	1.18
30°	1.21

Constants for Z_{thJK} calculation:

i	R _{thi} [K/W]	t _i [s]
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.1910
4	0.200	0.4500



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Электрон
Связь**

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Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литер Н,
помещение 100-Н Офис 331